

We focus on power.

Revision 1.01

13.01.2014

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DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode with integrated grating structure







General Product Information

Product	Application
760 nm DFB Laser with hermetic Butterfly Housing	Spectroscopy
Monitor Diode, Thermoelectric Cooler and Thermistor	O ₂ Detection
PM Fiber with angle-polished Connector	Metrology
High-reliable Package compliant for Space Applications	



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-40		85
Operational Temperature at Laser Chip	T_{LD}	°C	10		50
Forward Current	I _F	mA			130
Reverse Voltage	V_R	V			2
Output Power	P _{opt}	mW			12
TEC Current	I _{TEC}	А			1.8
TEC Voltage	V_{TEC}	V			3.2

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	-20		65
Operational Temperature at Laser Chip	T_LD	°C	15		35
Forward Current	I _F	mA			120
Output Power	P_{opt}	mW	2		10

Measurement Conditions / Comments
measured by integrated Thermistor
£l
ex fiber

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	759	760	761
Spectral Width (FWHM)	Δν	MHz		2	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dl	nm / mA		0.003	
Output Power @ I _F = 120 mA	P_{opt}	mW	10		

Measurement Conditions / Comments
see images on page 4
ex fiber





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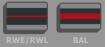
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Characteristics at T ₁₀ = 25 °C at E	Begin Of Life cont'd
Cildi actel istics at i i n - E5 Cat E	

Parameter	Symbol	Unit	min	typ	max
Slope Efficiency	S	W/A	0.1	0.2	0.3
Threshold Current	I _{th}	mA			70
Polarization Extinction Ratio	PER	dB		10	
Sidemode Supression Ratio	SMSR	dB	30	45	
Mode-hop free Operating Range (SMSR > 30 dl	3)				
Variant 0 (see order code scheme)	T_{LD}	° C		25	
	P_{opt}	mW		10	
Variant 1 (see order code scheme)	T_{LD}	° C		25	
	P_{opt}	mW	2		10
Variant 2 (see order code scheme)	T_{LD}	° C	15		35
	P_{opt}	mW	2		10

Measurement Conditions / Comments				
P _{opt} =	10 mW			
see bel	ow			
temper	ature measured by integrated themistor			
temper	ature measured by integrated themistor			
temper	ature measured by integrated themistor			

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{ont}	uA/mW	6		120

Measurement Conditions / Comments
$P_{opt} = 2 \ldots 10 \text{ mW, } U_{R \text{ MD}} = 5 \text{ V}$

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U_TEC	V		0.8	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments				
$P_{opt} = 10 \text{ mW},$	ΔT = 20 K			
$P_{opt} = 10 \text{ mW},$	$\Delta T = 20 \text{ K}$			
$P_{opt} = 10 \text{ mW},$	$\Delta T = 20 \text{ K}$			
$P_{opt} = 10 \text{ mW},$	$\Delta T = I T_{case} - T_{LD} I$			

Thermistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3976	







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Fiber and Connector Type

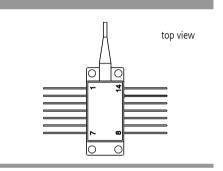
PM Fiber	900 / 125 / 5.5 μ m, UV/Polyester-elastomer Coating (l = 1 +/-0.1 m)
Connector	different variants available
	FC/APC (narrow key / 2mm)
	► SC/APC
	• other types on request

Measurement Conditions / Comments

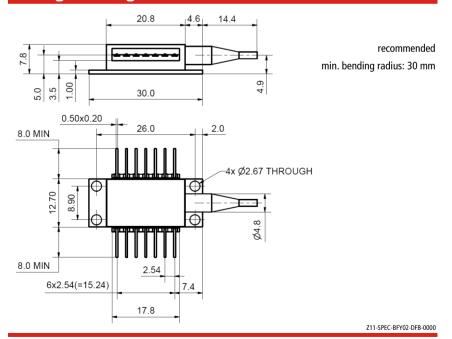
see order code scheme

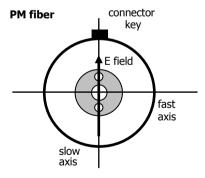
Package Pinout

1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	Photodiode (Anode)	12	not connected
4	Photodiode (Cathode)	11	Laser Diode (Cathode)
5	Thermistor	10	Laser Diode (Anode)
6	not connected	9	not connected
7	not connected	8	not connected



Package Drawings





slow axis of the PM fiber aligned to connector key

hermetically sealed Package:

Leak Rate < 5 · 10⁻⁸ atm.cc./s acc. MIL-STD-883E

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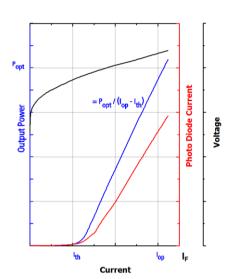




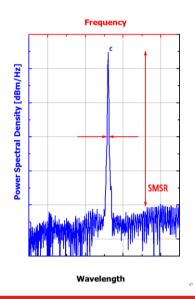


Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.



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Order Code Scheme

		n	

FC/APC (narrow key / 2mm)

SC/APC

other connector or fiber types upon request

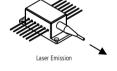
EYP-DFB-0760-00010-1500-BFY02-	0 x 0 x
	0
Variant 0	O
Variant 1	1
Variant 2	2

Mode-hop free Tuning Range (Minimum Side Mode Suppression Ratio > 30 dB)

$P_{opt} = 10 \text{ mW};$	$T_{LD} = 25^{\circ}$
$P_{opt} = 2 \dots 10 \text{ mW};$	$T_{LD} = 25^{\circ}$
$P_{opt} = 2 \dots 10 \text{ mW};$	T _{LD} = 15 35°

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.





The DFB diode type is known to be sensitive against optical feedback, so an optical isolator may be required in some cases. Operating at moderate temperatures on a proper metal heat sinks will contribute to stable operation and a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.









